

6501130 NATL SEMICONDUCTOR (DISCRETE)

28C 35542

T-31-01



PRO ELECTRON SERIES (Continued)

Type No.	Case Style	V _{CE(S)} (V) Min	V _{CEO} (V) Min	V _{EB0} (V) Min	I _{CE(S)} (mA) Max	V _{CB} (V)	h _{FE} 1 kHz* @ I _C & V _{CE}		V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) Min Max @ I _C (mA)		C _{ob} (pF) Max	f _T (MHz) @ I _C (mA)		t _{off} (ns) Max	NF (dB) Max	Test Conditions	Process No.			
							Min	Max		Min	Max		Min	Max							
BF254	TO-92 (98)	30	20	5	100	20	67	220	1	10	0.65	0.74*	1	0.34		1		3.5	7	46	
BF255	TO-92 (98)	30	20	-5	100	20	36	125	1	10	0.65	0.74*	1	0.34		1		3.5	7	46	
BF257	TO-39	100	100	5	50	100	25	30	10	10	1.0	0.65	0.74*	30	0.34		1		3.5	7	48
BF258	TO-39	250	250	5	50	200	25	30	10	10	1.0	0.65	0.74*	30	0.34		1		3.5	7	48
BF259	TO-39	300	300	5	50	250	25	30	10	10	1.0	0.65	0.74*	30	0.34		1		3.5	7	48
BF457	TO-126	100	100	5	50	100	25	30	10	10	1.0	0.65	0.74*	30	0.34		1		3.5	7	48
BF458	TO-126	250	200	5	50	200	25	30	10	10	1.0	0.65	0.74*	30	0.34		1		3.5	7	48
BF459	TO-126	300	300	5	50	250	25	30	10	10	1.0	0.65	0.74*	30	0.34		1		3.5	7	48
BFX13	TO-18	20	15	5	50	15	10	100	2	0.35	0.2	0.78	1	6	150	10		10	8	66	
BFX29	TO-5	20	15	5	50	50	40	150	10	0.4	0.25	0.7	0.9	10	100	50	150		9	63	
BFX30	TO-5	65	65	5	50	50	40	10	0.4	0.4	0.9	1.3	30	12		290		4	63		
BFX37	TO-18	60	60	6	20†	50	100	10	5	0.4	0.25	0.9	10	6	40	0.5		3	1	62	
BFX65	TO-18	45	45	6	10*	40	100	10	5	0.25	0.25	0.9	10	6.5				3	1	62	

TEST CONDITIONS:
 (1) I_C = 200 μA, V_{CE} = 5V, f = 1 kHz. (2) I_C = 100 mA, V_{CC} = 20V, I_B¹ = I_B² = 5 mA. (3) I_C = 200 μA, V_{CE} = 2V, f = 1 kHz. (4) I_C = 100 mA, V_{CC} = 10V, I_B¹ = I_B² = 10 mA. (5) I_C = 10 mA, V_{CC} = 3V, I_B¹ = I_B² = 1 mA. (6) I_C = 100 μA, V_{CE} = 5V, f = 1 kHz. (7) I_C = 1 mA, V_{CE} = 10V, f = 200 kHz. (8) I_C = 1 mA, V_{CE} = 5V, f = 1 kHz. (9) I_C = 150 mA, V_{CC} = 6V, I_B¹ = I_B² = 15 mA. (10) I_C = 10 μA, V_{CE} = 5V, f = WB.



Pro Electron Series

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